

N-channel TrenchMOS logic level FET 28 July 2016

Product data sheet

1. General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with VGS(th) rating of greater than 0.5V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	324	W
Static charact	eristics			1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	2.29	2.8	mΩ
Dynamic char	acteristics	·					
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 48 V; <u>Fig. 13; Fig. 14</u>		-	28.6	-	nC

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UITA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK962R8-60E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK962R8-60E	BUK962R8-60E

8. Limiting values

Table 5.Limiting values

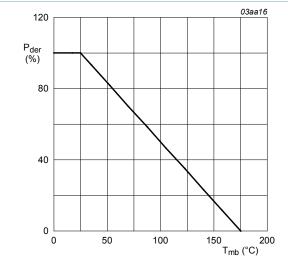
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \text{ °C}; \text{ Pulsed}$	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	324	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[3]	-	120	A
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[3]	-	120	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	917	А
T _{stg}	storage temperature			-55	175	°C
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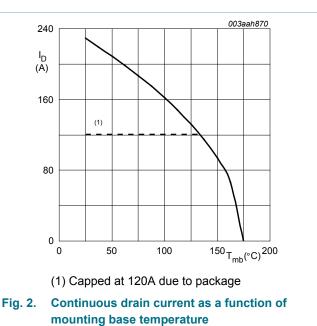
Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[3]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	917	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 120 \text{ A}; \text{V}_{\text{sup}} \leq 60 \text{V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 5 \text{V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[4][5]	-	519	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm [1]
- [2] Significantly longer life times are achieved by lowering T_{j} and or V_{GS}
- [3] Continuous current is limited by package.
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information. [4]
- [5]



Normalized total power dissipation as a Fig. 1. function of mounting base temperature

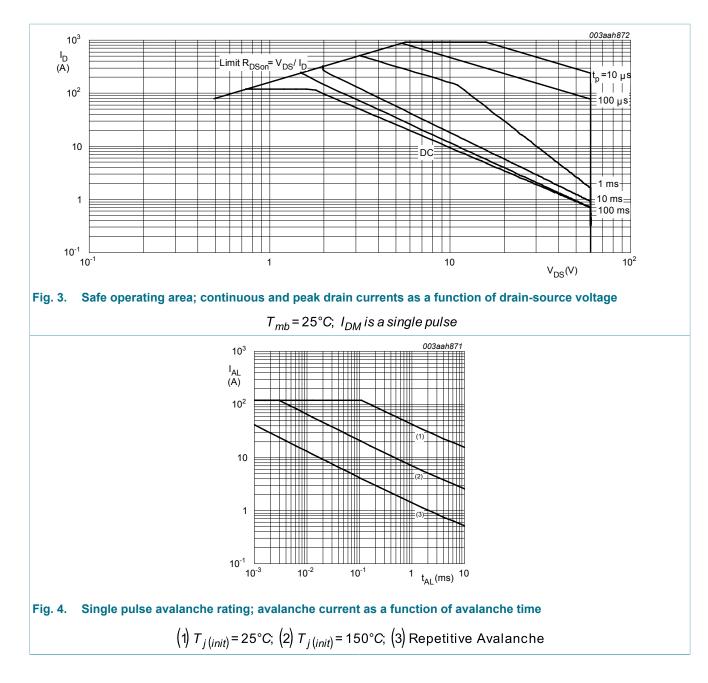
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



 $V_{GS} \ge 5V$

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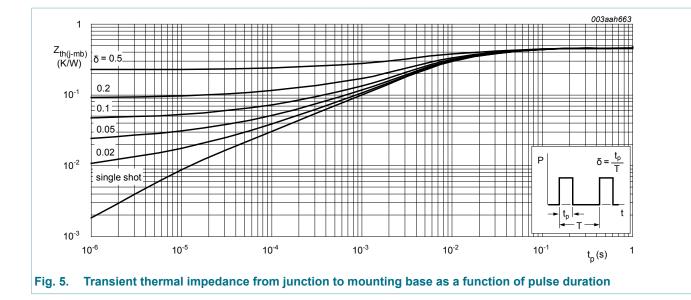
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.46	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

Table 6. Thermal characteristics

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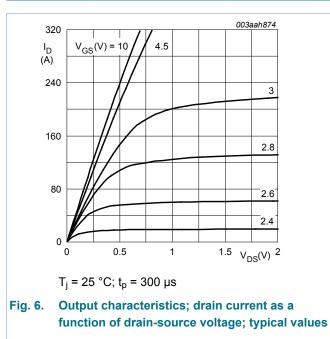


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.08	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	1 µ 500 µ 100 r 100 r	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	2.29	2.8	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	2.08	2.5	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	6.2	mΩ
Dynamic ch	aracteristics		1			
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 48 V; V_{GS} = 5 V;	-	96	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	27.8	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q _{GD}	gate-drain charge		-	28.6	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	11701	15600	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 25 \text{ V}; \text{ f} = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ Fig. 15}$ $V_{DS} = 45 \text{ V}; \text{ R}_L = 1.8 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega$ from upper edge of drain mounting base to center of die from source lead to source bonding pad $I_S = 25 \text{ A}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ Fig. 16}$ $I_S = 20 \text{ A}; \text{ d}_S/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	925	1110	pF
C _{rss}	reverse transfer capacitance		-	444	610	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 5 V;	-	53	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	88	-	ns
t _{d(off)}	turn-off delay time		-	115	-	ns
t _f	fall time		-	81	-	ns
L _D	internal drain inductance		-	2.5	-	nH
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode					,
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;	-	45	-	ns
Qr	recovered charge	$T_{j} = 25 \text{ °C}; \text{ Fig. 15}$ $V_{DS} = 45 \text{ V}; \text{ R}_{L} = 1.8 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega$ from upper edge of drain mounting base to center of die from source lead to source bonding pad $I_{S} = 25 \text{ A}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ Fig. 16}$	-	74	-	nC



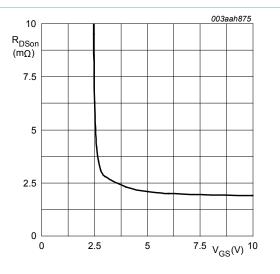
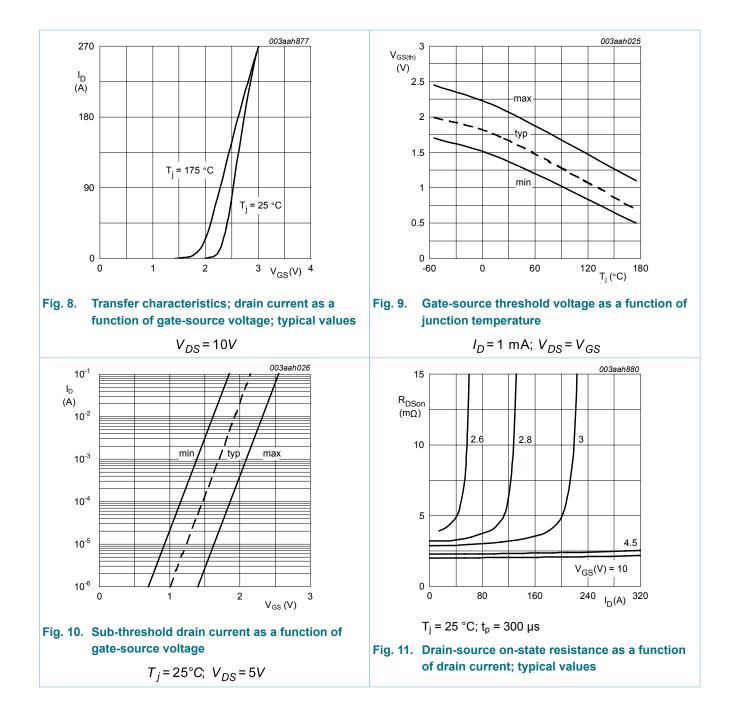


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$

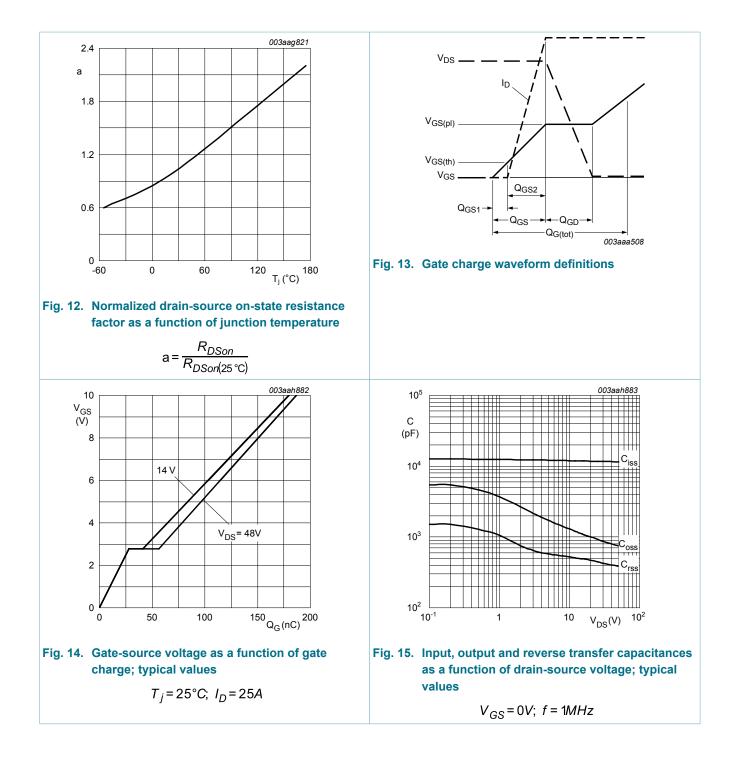
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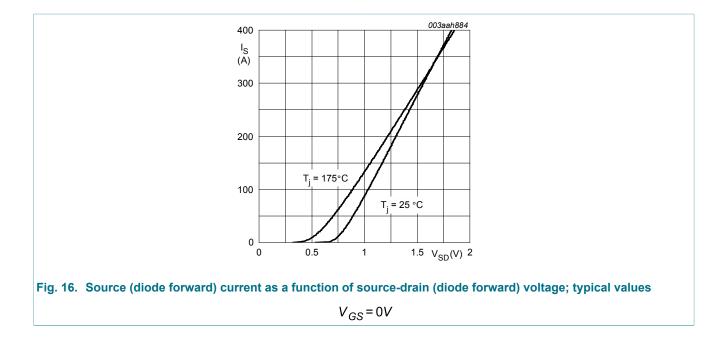
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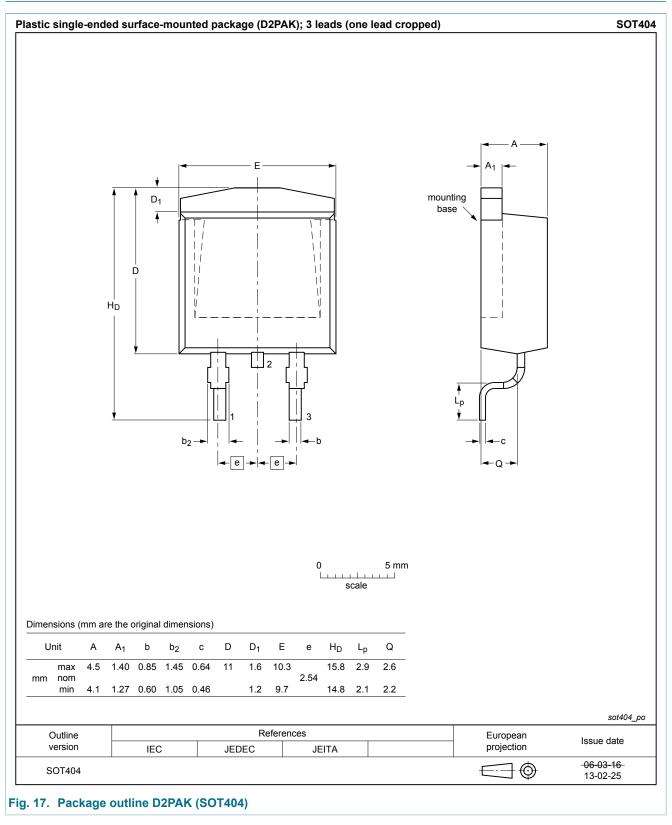
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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